

Abraham Arias

List of Publications by Year in descending order

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16
papers

151
citations

1307594

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1125743

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docs citations

16
times ranked

277
citing authors

#	ARTICLE	IF	CITATIONS
1	Ultrahigh purity beta gallium oxide microstructures. <i>Ceramics International</i> , 2022, 48, 25322-25325.	4.8	5
2	UV Sensitivity of MOS Structures with Silicon Nanoclusters. <i>Sensors</i> , 2019, 19, 2277.	3.8	7
3	Synthesis of high purity nickel oxide by a modified sol-gel method. <i>Ceramics International</i> , 2019, 45, 11403-11407.	4.8	27
4	Structural, Optical, and Electrical Characterization of In^{2+} -Ga ₂ O ₃ Thin Films Grown by Plasma-Assisted Molecular Beam Epitaxy Suitable for UV Sensing. <i>Advances in Materials Science and Engineering</i> , 2018, 2018, 1-6.	1.8	18
5	Gold, copper and gold/copper bimetallic nanoparticles obtained by focused ion beam sputter deposition and rapid thermal annealing. <i>Vacuum</i> , 2018, 157, 166-172.	3.5	10
6	Structural and electrical characterization of multilayer Al ₂ O ₃ /ZnO nanolaminates grown by atomic layer deposition. <i>Materials Science in Semiconductor Processing</i> , 2017, 71, 290-295.	4.0	14
7	Structural and optical properties of In^{2+} -Ga ₂ O ₃ thin films grown by plasma-assisted molecular beam epitaxy. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2016, 34, .	1.2	46
8	Application of Metal-Oxide-Semiconductor structures containing silicon nanocrystals in radiation dosimetry. <i>Open Physics</i> , 2015, 13, .	1.7	8
9	Structural, compositional and electrical characterization of Si-rich SiO _x layers suitable for application in light sensors. <i>Materials Science in Semiconductor Processing</i> , 2015, 37, 229-234.	4.0	7
10	UV Dosimeters Based on Metal-Oxide-Semiconductor Structures Containing Si Nanocrystals. <i>Sensor Letters</i> , 2015, 13, 561-564.	0.4	2
11	Application of Metal-Oxide-Semiconductor Structures for Visible and Near UV Light Sensing. <i>Sensor Letters</i> , 2015, 13, 556-560.	0.4	0
12	Visible Light Sensor Based on Metal-Oxide-Semiconductor Structure. <i>Key Engineering Materials</i> , 2014, 605, 384-387.	0.4	1
13	Electrical Characterization of Interface Defects in MOS Structures Containing Silicon Nanoclusters. <i>Advanced Materials Research</i> , 2014, 976, 129-132.	0.3	1
14	TEM and Spectroscopic Ellipsometry studies of multilayer gate dielectrics containing crystalline and amorphous Si nanoclusters. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2013, 51, 111-114.	2.7	4
15	Electrical Characterization of MOS Structures with Silicon Nanocrystals Suitable for X-Ray Detection. <i>Key Engineering Materials</i> , 0, 543, 150-153.	0.4	0
16	MOS Structures Containing Si Nanocrystals for Applications in UV Dosimeters. <i>Key Engineering Materials</i> , 0, 605, 380-383.	0.4	1